



# DCP56/-16

### NPN SURFACE MOUNT TRANSISTOR

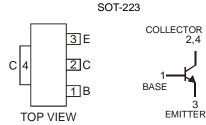
### **Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DCP53)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

## **Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)





Schematic and Pin Configuration

# **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Collector-Base Voltage	$V_{CBO}$	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	Ic	1	А

### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @ T <sub>A</sub> = 25°C (Note 3)	$P_d$	1	W
Operating and Storage Temperature Range	$T_j$ , $T_{STG}$	-55 to 150	°C
Thermal Resistance, Junction to Ambient Air @T <sub>A</sub> = 25°C (Note 3)	$R_{ hetaJA}$	125	°C/W

# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)		•		•		
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	100	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	80	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	5.0	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector-Base Cutoff Current	I <sub>CBO</sub>	_	_	0.1 20	μА	$V_{CB} = 30V, I_E = 0$ $V_{CB} = 30V, I_E = 0, T_A = 150$ °C
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	10	μΑ	$V_{EB} = 5.0V, I_C = 0$
ON CHARACTERISTICS (Note 4)						
DC Current Gain	h <sub>FE</sub>	25 40 25		 250 	_	$I_C = 5.0$ mA, $V_{CE} = 2.0$ V $I_C = 150$ mA, $V_{CE} = 2.0$ V $I_C = 500$ mA, $V_{CE} = 2.0$ V
DCP56-16		100	160	250		$I_C = 150 \text{mA}, \ V_{CE} = 2.0 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	0.5	V	I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
Base-Emitter Turn-On Voltage	V <sub>BE (ON)</sub>	_	_	1.0	V	$I_C = 500$ mA, $V_{CE} = 2.0$ V
SMALL SIGNAL CHARACTERISTICS						
Current-Gain-Bandwidth Product	f <sub>T</sub>	_	200	_	MHz	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5.0V, f = 100MHz

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Pulse Test: Pulse width =  $\leq 300 \mu s$ , Duty Cycle  $\leq 2\%$ .



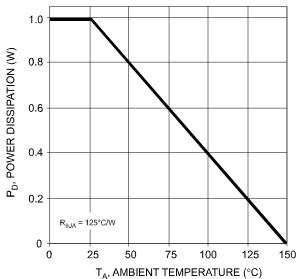
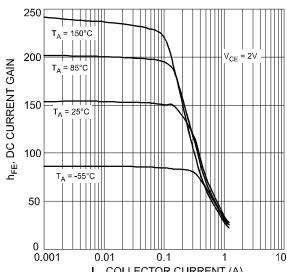
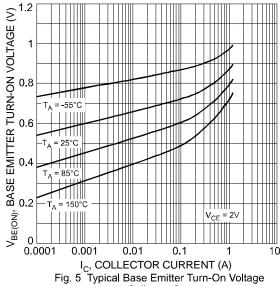


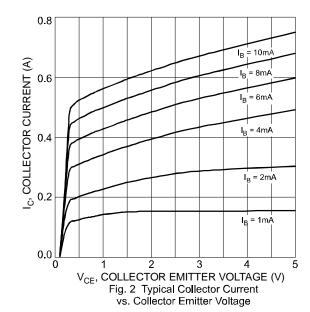
Fig. 1 Power Dissipation vs. Ambient Temperature



 ${\rm I_C}$ , COLLECTOR CURRENT (A) Fig. 3 Typical DC Current Gain vs. Collector Current



vs. Collector Current



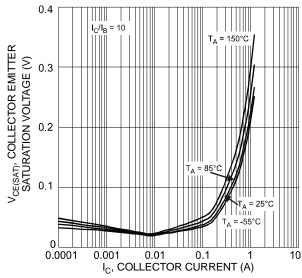


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

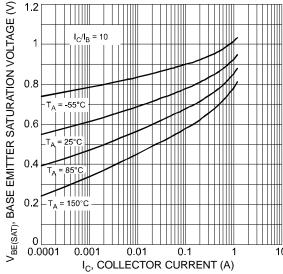
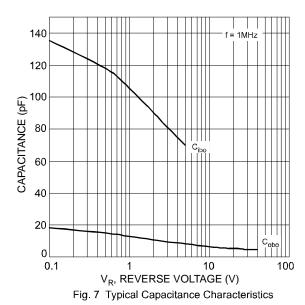
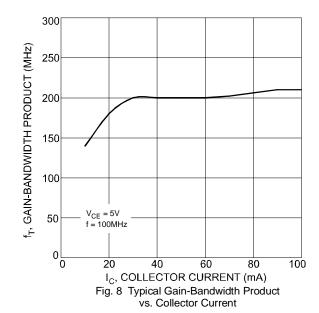


Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current





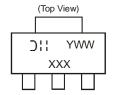


#### **Ordering Information** (Note 5)

Device	Packaging	Shipping
DCP56-13	SOT-223	2500/Tape & Reel
DCP56-16-13	SOT-223	2500/Tape & Reel

5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

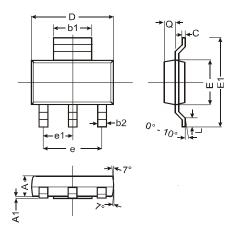
# **Marking Information**



XXX = Product Type Marking Code ex. N18 = DCP56 N18-16 = DCP56-16

☐☐ = Manufacturer's Marking Code YWW = Date Code Marking Y = Last Digit of Year ex: 7 = 2007WW = Week Code 01-52

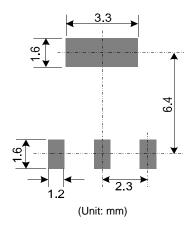
# **Package Outline Dimensions**



SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е			4.60		
e1			2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					



# Suggested Pad Layout: (Based on IPC-SM-782)



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